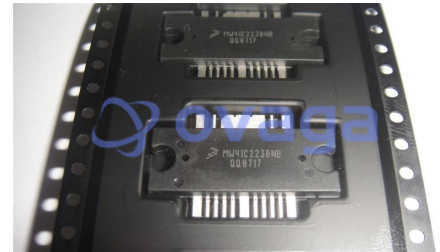


RF LDMOS Wideband Integrated Power Amplifiers, RF Amplifier 2.1GHZ 28V TO272WBN



Images are for reference only

Manufacturers	NXP Semiconductor
Package/Case	TO-272 WB-16
Product Type	RF Integrated Circuits
RoHS	Rohs
Lifecycle	

Please submit RFQ for MW4IC2230NBR1 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

MW4IC2230NBR1 is a specific part number for a high-frequency RF transistor. It is a gallium nitride (GaN) HEMT (High Electron Mobility Transistor) device manufactured by NXP Semiconductors.

Features

Operating frequency range: 2300-2400 MHz

Output power: 30 Watts

Power gain: 15 dB

Drain efficiency: 65%

Integrated ESD protection

RoHS compliant

Application

Qorvo: QPD1000

Cree: CGHV27300F

Infineon: PGA26E19BA

MACOM: MAGX-001090-030L00



Related Products



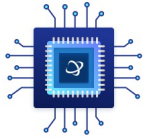
[MW7IC2040NR1](#)

NXP Semiconductor
TO-270-16



[MW7IC2725NBR1](#)

NXP Semiconductor
TO-272



[MW7IC2040NBR1](#)

NXP Semiconductor
HV71990MHZT



[MHVIC915NR2](#)

NXP Semiconductor
PFP-16



[RC522](#)

NXP Semiconductor
QFN-32



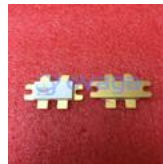
[74HC4046AD](#)

NXP Semiconductor
SO-16



[SA636DK/01](#)

NXP Semiconductor
SSOP-20



[BLF278C](#)

NXP Semiconductor
SOT-262